COMPLIANT

HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt®



| PRIMARY CHARACTERISTICS | | | | |
|----------------------------------|-------------|--|--|--|
| I _{F(AV)} | 15 A | | | |
| V _R | 600 V | | | |
| V _F at I _F | 1.25 V | | | |
| t _{rr} (typ.) | 21 ns | | | |
| T _J max. | 175 °C | | | |
| Package | 2L TO-220AC | | | |
| Circuit configuration | Single | | | |

FEATURES

- Hyperfast soft recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Peak repetitive reverse voltage | V _{RRM} | | 600 | V | |
| Average rectified forward current in DC | I _{F(AV)} | T _C = 149 °C | 15 | ۸ | |
| Non-repetitive peak surge current | I _{FSM} | T _J = 25 °C | 160 | Α | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -65 to +175 | °C | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|--|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | Ι _R = 100 μΑ | 600 | - | - | |
| Forward voltage V _F | I _F = 15 A | - | 1.8 | 2.45 | V | |
| | I _F = 15 A, T _J = 150 °C | - | 1.25 | 1.6 | | |
| Devene leekene euwent | | $V_R = V_R$ rated | - | 0.01 | 15 | |
| Reverse leakage current | I _R | T _J = 150 °C, V _R = V _R rated | - | 20 | 200 | μA |
| Junction capacitance | C _T | V _R = 600 V - 12 - | | pF | | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body - 8 - | | nH | | |

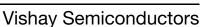


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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---|------------------------|---|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | | $I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 21 | 26 | |
| Reverse recovery time | | $I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 25 | 36 | |
| neverse recovery time | t _{rr} | T _J = 25 °C | | - | 29 | - | ns |
| | | T _J = 125 °C | | - | 65 | - | |
| Deel and a second second | T _J = 25 °C | I _F = 15 A, dI _F /dt = 200 A/μs, | - | 3.9 | - | Α | |
| Peak recovery current | I _{RRM} | T _J = 125 °C | $V_{R} = 390 \text{ V}$ | - | 7.0 | - | |
| Deviana nagavani abansa | Q _{rr} | T _J = 25 °C | | - | 60 | - | nC |
| Reverse recovery charge | | T _J = 125 °C | | - | 240 | - | nc |
| Reverse recovery time | t _{rr} | T _J = 125 °C | I _F = 15 A, dI _F /dt = 800 A/μs, V _R = 390 V | - | 42 | - | ns |
| Peak recovery current | I _{RRM} | | | - | 21 | - | Α |
| Reverse recovery charge | Q _{rr} | | | - | 480 | - | nC |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|--|----------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C |
| Thermal resistance, junction-to-case | R _{thJC} | | - | 1.2 | 1.4 | |
| Thermal resistance, junction-to-ambient | R _{thJA} | Typical socket mount | | 70 | °C/W | |
| Typical thermal resistance, case-to-heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | |
| Weight | | | - | 2 | - | g |
| Weight | | | - | 0.07 | - | oz. |
| Mounting torque | | | 6 (5) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking device | | Case style 2L TO-220AC | ETH1506 | | | |





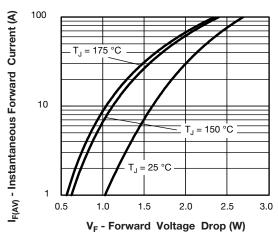


Fig. 1 - Typical Forward Voltage Drop Characteristics

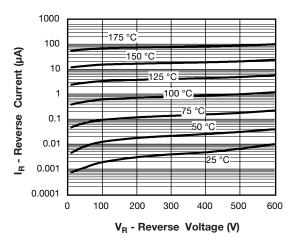


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

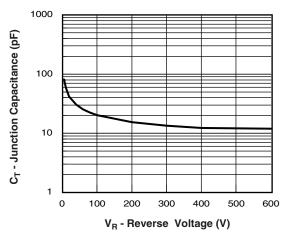


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

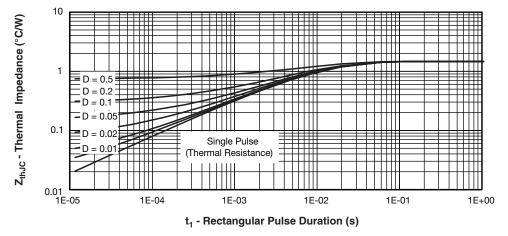


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Average Power Loss (W)

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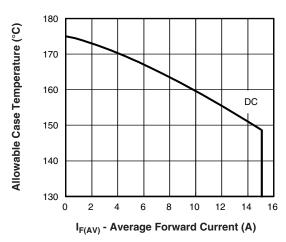
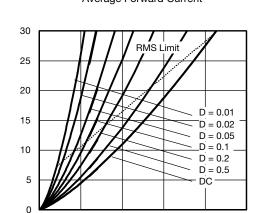


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current



I_{F(AV)} - Average Forward Current (A)
Fig. 6 - Forward Power Loss Characteristics

15

20

25

10

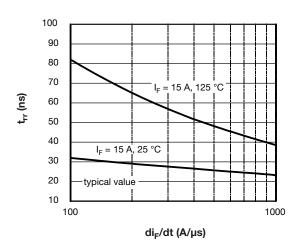


Fig. 7 - Typical Reverse Recovery vs. dI_F/dt

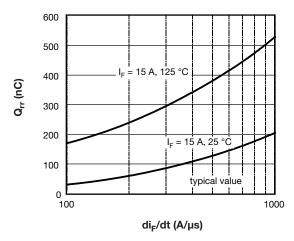
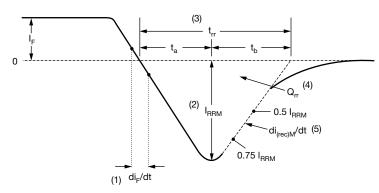


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

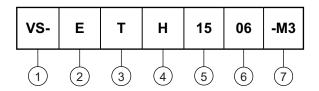
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Circuit configuration:

E = single

3 - T = 2L TO-220AC

H = hyperfast recovery time

5 - Current code: 15 = 15 A

Voltage code: 06 = 600 V

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | |
|--------------------------------|-------------------|------------------------|-------------------------|--|--|
| PREFERRED P/N | QUANTITY PER TUBE | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | |
| VS-ETH1506-M3 | 50 | 1000 | Antistatic plastic tube | | |

| LINKS TO RELATED DOCUMENTS | | | | |
|--|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?96156</u> | | | | |
| Part marking information | www.vishay.com/doc?95391 | | | |



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